

# 2SA1018

Silicon PNP epitaxial planer type

For general amplification

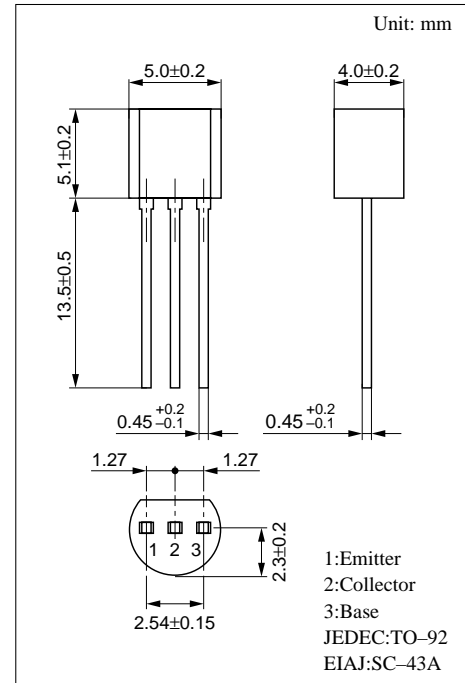
Complementary to 2SC1473

## Features

- High collector to emitter voltage  $V_{CEO}$ .

## Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	-250	V
Collector to emitter voltage	$V_{CEO}$	-200	V
Emitter to base voltage	$V_{EBO}$	-5	V
Peak collector current	$I_{CP}$	-100	mA
Collector current	$I_C$	-70	mA
Collector power dissipation	$P_C$	750	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 ~ +150	°C



## Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CEO}$	$V_{CE} = -120V, I_B = 0, T_a = 60^\circ C$			-1	$\mu A$
Collector to emitter voltage	$V_{CEO}$	$I_C = -100\mu A, I_B = 0$	-200			V
Emitter to base voltage	$V_{EBO}$	$I_E = -1\mu A, I_C = 0$	-5			V
Forward current transfer ratio	$h_{FE}^*$	$V_{CE} = -10V, I_C = -5mA$	60		220	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50mA, I_B = -5mA$			-1.5	V
Transition frequency	$f_T$	$V_{CB} = -10V, I_E = 10mA, f = 200MHz$	50			MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$			10	pF

\* $h_{FE}$  Rank classification

Rank	Q	R
$h_{FE}$	60 ~ 150	100 ~ 220

